

# Schottky barrier diode

## RB520S-30 New

### ●Applications

Low current rectification and high speed switching

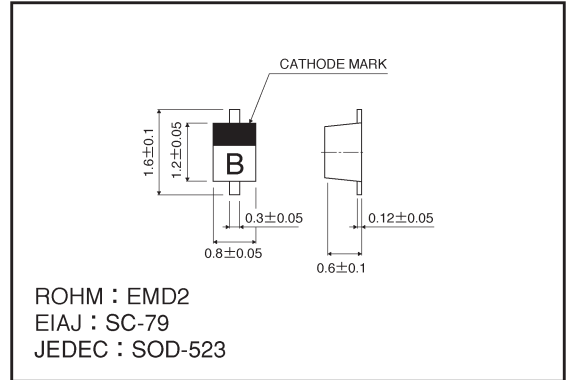
### ●Features

- 1) Small surface mounting type.(EMD2)
- 2) High reliability.
- 3) Low reverse current and low forward voltage.  
(actual capability :  $1\mu\text{A}$ )

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Units: mm)



### ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	$V_R$	30	V
Mean rectifying current	$I_o$	200	mA
Peak forward surge curren*	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40~+125	°C

\*60 Hz for 1  $\sim$

### ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	—	0.50	0.60	V	$I_F=200\text{mA}$
Reverse current	$I_R$	—	0.1	1.0	$\mu\text{A}$	$V_R=10\text{V}$

\*ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C)

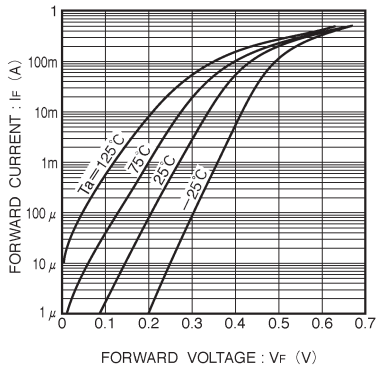


Fig. 1 Forward characteristics

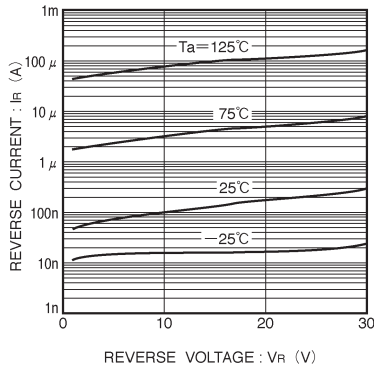


Fig. 2 Reverse characteristics

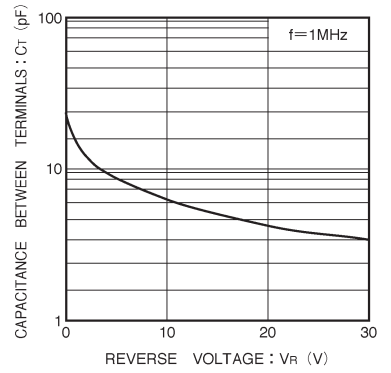


Fig. 3 Capacitance between terminals characteristics

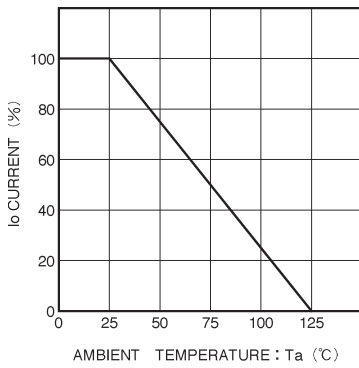


Fig. 4. Derating curve (mounting on glass epoxy PCBs)